NSN 5962-01-296-1084

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output and 125.00 nanoseconds propagation delay time, high to low level

View Online at https://aerobasegroup.com/nsn/5962-01-296-1084

view Online at https://aeiobasegroup.com/hsil/5962-01-296-1064
Body Length:
0.960 inches
Body Width:
Between 0.220 inches and 0.310 inches
Body Height:
Between 0.140 inches and 0.185 inches
Maximum Power Dissipation Rating:
950.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Hermetically sealed and burn in and programmable and bipolar and schottky
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
12 input
Case Outline Source And Designator:
D-6 mil-m-38510
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 7.0 volts power source
Time Rating Per Chacteristic:
125.00 nanoseconds propagation delay time, low to high level output and 125.00 nanoseconds propagation delay t
output
Memory Device Type:
Rom
Memory Capacity:
Unknown
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
18 printed circuit
Shelf Life:
N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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